

14. A process for removing photoresist according to claim 13, wherein the photoresist is g-line, i-line, deep UV, E-beam or X-ray.
15. A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.
16. A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for 10 minutes.
17. A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at 1 atm.
18. A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.
19. A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of 120 degrees C.
20. A process for removing photoresist after drywall etching according to claim 13, wherein the fluorine containing compound is hydrofluoric acid.
21. A process for removing photoresist after drywall etching according to claim 20, wherein the ratio of sulfuric acid to hydrofluoric acid and hydrogen peroxide is 3:1 by volume.